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### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Jean-Pierre Joly et al.

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### THIRD SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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following reference(s):

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Plaintiff's Reply in Support of their Motion for Judgment on SiGen's Indefiniteness Defense dated July 25, 2002
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Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated January 28, 2003
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Combined Petition for Panel Rehearing and for Rehearing En Banc by Plaintiffs-Appellant's Soitec, S.A. and Commissariat A L'Energie Atomique, dated December 10, 2003.
Order [dated January 7, 2004 denying Appellants' petition for panel rehearing and Appellant's petition for rehearing en banc].
Judgment Mandate [dated January 14, 2004].
MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/20/2009). CORRECTING ENTRY: Docket clerk deleted D.I. 78 (opening brief) due to document being filed improperly. Counsel is advised to re-file document using the OPENING BRIEF event code rather than the combined opening and answering brief event code. (lid) (Entered: 10/21/2009)

OPENING BRIEF in Support re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 11/9/2009. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C)(Rogowski, Patricia) (Entered: 10/21/2009)
Cross MOTION to Bifurcate all Collateral Issues - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues, <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique.Reply Brief due date per Local Rules is 11/20/2009. (Attachments: # <u>1</u> Exhibit, # <u>2</u> Exhibit, # <u>3</u> Exhibit, # <u>4</u> Exhibit, # <u>5</u> Exhibit, # <u>6</u> Exhibit, # <u>7</u> Exhibit, # <u>8</u> Exhibit, # <u>9</u> Exhibit, # <u>10</u> Exhibit, # <u>11</u> Exhibit, # <u>12</u> Declaration, # <u>13</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3)(Rogowski, Patricia) (Entered: 11/17/2009)
ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 12/3/2009. (Rogowski, Patricia) (Entered: 11/19/2009)
REPLY BRIEF re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit Declaration of Marcus T. Hall in Support of Plaintiffs' Reply Re: Cross-Motion to Bifurcate all Collateral Issues)(Kraft, Denise) (Entered: 12/03/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production of Three Boxes of Wafer Samples by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/08/2009). Set Hearings: Discovery Conference set for 12/21/2009 04:00 PM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 12/09/2009).
MOTION for Leave to File Stipulated Motion for Leave to File a Sur-Reply Brief in Support of MEMC's Motion to Bifurcate - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 12/14/2009)
SUR-REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order MEMC's SUR-REPLY BRIEF IN SUPPORT OF ITS MOTION TO BIFURCATE THE ISSUES OF WILLFULNESS AND DAMAGES FOR PURPOSES OF DISCOVERY AND TRIAL filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/16/2009)
MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/07/2010)
OPENING BRIEF in Support re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 5/24/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6, # <u>7</u> Exhibit 7, # <u>8</u> Exhibit 8, # <u>9</u> Exhibit 9, # <u>10</u> Exhibit 10, # <u>11</u> Exhibit 11, # <u>12</u> Exhibit 12, # <u>13</u> Exhibit 13, # <u>14</u> Exhibit 14, # <u>15</u> Exhibit 15)(Rogowski, Patricia) (Entered: 05/07/2010)

ANSWERING BRIEF in Opposition re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. Reply Brief due date per Local Rules is 6/4/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
DECLARATION re <u>145</u> Answering Brief in Opposition,, Declaration of Marcus T. Hall in Support of Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
REPLY BRIEF IN SUPPORT OF <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6)(Rogowski, Patricia) Modified on 6/4/2010 (lid). (Entered: 06/04/2010)
STATEMENT re <u>148</u> Stipulation Joint Claim Construction Statement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
CLAIM Construction Chart by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
SUR-REPLY BRIEF re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)
DECLARATION re <u>157</u> Sur-Reply Brief, Declaration of Marcus T. Hall in Support of Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)



CLAIM CONSTRUCTION OPENING BRIEF filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0001-DA0006, # 2 Appendix DA0007-DA0032, # 3 Appendix DA0033-DA0072, # 4 Appendix DA0073-DA0112, # 5 Appendix DA0113-DA0152, # 6 Appendix DA0153-DA0192, # 7 Appendix DA0193-DA0232, # 8 Appendix DA0233-DA0272, # 9 Appendix DA0273-DA0312, # 10 Appendix DA0313-DA0352, # 11 Appendix DA0353-DA0392, # 12 Appendix DA0393-DA0432, # 13 Appendix DA0433-DA0472, # 14 Appendix DA0473-DA0512, # 15 Appendix DA0513-DA0521, # 16 Appendix DA0522-DA0545, # 17 Appendix SEALED - DA0546-DA0551, # 18 Appendix DA0552-DA0563, # 19 Appendix SEALED - DA0564-DA0566, # 20 Appendix DA0567-DA0573, # 21 Appendix SEALED - DA0574-DA0599, # 22 Appendix DA0600-DA0604, # 23 Appendix DA0605-DA0609, # 24 Appendix DA0610-DA0625, # 25 Appendix DA0626-0634, # 26 Appendix DA0635, # 27 Appendix DA0636-DA0652, # 28 Appendix SEALED - DA0653-DA0657, # 29 Appendix DA0658-DA0667, # 30 Appendix DA0668-DA0670, # 31 Appendix DA0671-DA0678, # 32 Appendix DA0679-DA0687, # 33 Appendix DA0688-DA0696, # 34 Appendix SEALED - DA0697-DA0705, # 35 Appendix SEALED - DA0706-DA0711, # 36 Appendix SEALED - DA0712-DA0714, # 37 Appendix DA0715-DA0717, # 38 Appendix DA0718-DA0719, # 39 Appendix DA0720-DA0722, # 40 Appendix DA0723-DA0732, # 41 Appendix DA0733-DA0740, # 42 Appendix DA0741-DA0749, # 43 Appendix DA0750-DA0769, # 44 Appendix DA0770-DA0781)(Rogowski, Patricia) (Entered: 06/25/2010)

CLAIM CONSTRUCTION OPENING BRIEF Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

DECLARATION re 168 Claim Construction Opening Brief, Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

APPENDIX re 167 Claim Construction Opening Brief,,,,, by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA-0001 - DA-0006, # 2 Appendix DA-0007 - DA-0032, # 3 Appendix DA-0033 - DA-0072, # 4 Appendix DA-0073 - DA-0112, # 5 Appendix DA-0113 - DA-0152, # 6 Appendix DA-0153 - DA-0192, # 7 Appendix DA-0193 - DA-0232, # 8 Appendix DA-0233 - DA-0272, # 9 Appendix DA-0273 - DA-0312, # 10 Appendix DA-0313 - DA-0352, # 11 Appendix DA-0353 - DA-0392, # 12 Appendix DA-0393 - DA-0432, # 13 Appendix DA-0433 - DA-0472, # 14 Appendix DA-0473 - DA-0512, # 15 Appendix DA-0513 - DA-0521)(Rogowski, Patricia) (Entered: 06/28/2010)

REDACTED VERSION of 175 Appendix by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0522-DA0545, # 2 Appendix DA0546-DA0551, # 3 Appendix DA0552-DA0563, # 4 Appendix DA0564-DA0566, # 5 Appendix DA0567-DA0573, # 6 Appendix DA0574-DA0599, # 7 Appendix DA0600-DA0604, # 8 Appendix DA0605-DA0609, # 9 Appendix DA0610-DA0625, # 10 Appendix DA0626-DA0634, # 11 Appendix DA0635, # 12 Appendix DA0636-DA0652, # 13 Appendix DA0653-DA0657, # 14 Appendix DA0658-DA0667, # 15 Appendix DA0668-DA0670, # 16 Appendix DA0671-DA0678, # 17 Appendix DA0679-DA0687, # 18 Appendix DA0688-DA0696, # 19 Appendix DA0697-DA0705, # 20 Appendix DA0706-DA-0711, # 21 Appendix DA0712-DA0714, # 22 Appendix DA0715-DA0717, # 23 Appendix DA0718-DA0719, # 24 Appendix DA0720-DA0722, # 25 Appendix DA0723-DA0732, # 26 Appendix DA0733-DA0740, # 27 Appendix DA0741-DA0749, # 28 Appendix DA0750-DA0769, # 29 Appendix DA0770-DA0781, # 30 Certificate of Service)(Rogowski, Patricia) (Entered: 06/28/2010)

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) Vol. I - JA0001 to JA0533. APPENDIX VOL I. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (2) Vol. II - JA0534 to JA0930. APPENDIX VOL II. re 173 Notice of Filing Paper Documents(OVERSIDED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).
NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (3) Vol. III – JA0931 to JA1502. APPENDIX VOL III. re 173 Notice of Filing Paper Documents(OVERSIDED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010) (2 parts).
NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (4) Vol. IV – JA1503 to JA1510. APPENDIX VOL IV. re <u>173</u> Notice of Filing Paper Documents, (OVERSIDED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).
NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (5) Vol. V – JA1511 to JA2089 (2 parts) Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010).
MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>187</u> MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Rogowski, Patricia) (Entered: 07/02/2010)
APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix Vol. II of XIX, # <u>2</u> Appendix Vol. III of XIX, # <u>3</u> Appendix Vol. IV of XIX, # <u>4</u> Appendix Vol. V of XIX, # <u>5</u> Appendix Vol. VII of XIX, # <u>6</u> Appendix Vol. IX of XIX, # <u>7</u> Appendix Vol. XI of XIX, # <u>8</u> Appendix Vol. XII of XIX, # <u>9</u> Appendix Vol. XIII of XIX, # <u>10</u> Appendix Vol. XIV of XIX, # <u>11</u> Appendix Vol. XV of XIX, # <u>12</u> Appendix Vol. XVI of XIX, # <u>13</u> Appendix Vol. XVIII of XIX, # <u>14</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Summary Judgment of Non-Infringement - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

OPENING BRIEF in Support re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)

OPENING BRIEF in Support re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>213</u> MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents filed by SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
REDACTED VERSION of <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)
REDACTED VERSION of <u>201</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0001 - MA0004, # <u>2</u> Appendix MA0005 - MA0010, # <u>3</u> Appendix MA0011 - MA0016, # <u>4</u> Appendix MA0017 - MA0020, # <u>5</u> Appendix MA0021 - MA0029, # <u>6</u> Appendix MA0030 - MA0045, # <u>7</u> Appendix MA0046 - MA0052, # <u>8</u> Appendix MA0053 - MA0078, # <u>9</u> Appendix MA0079 - MA0092, # <u>10</u> Appendix MA0093 - MA0129, # <u>11</u> Appendix MA0130 - MA0148, # <u>12</u> Appendix MA0149 - MA0160, # <u>13</u> Appendix MA0161 - MA0163, # <u>14</u> Appendix MA0164 - MA0167, # <u>15</u> Appendix MA0168 - MA0172, # <u>16</u> Appendix MA0173 - MA0183, # <u>17</u> Appendix MA0184 - MA0196, # <u>18</u> Appendix MA0197 - MA0207, # <u>19</u> Appendix MA0208 - MA0241, # <u>20</u> Appendix MA0242 - MA0245, # <u>21</u> Appendix MA0246 - MA0249, # <u>22</u> Appendix MA0250 - MA0252, # <u>23</u> Appendix MA0253 - MA0265, # <u>24</u> Appendix MA0266 - MA0281, # <u>25</u> Appendix MA0282 - MA0312, # <u>26</u> Appendix MA0313 - MA0359, # <u>27</u> Appendix MA0360 - MA0365, # <u>28</u> Appendix MA0366, # <u>29</u> Appendix MA0367 - MA0400, # <u>30</u> Appendix MA0401 - MA0474, # <u>31</u> Appendix MA0475 - MA0483, # <u>32</u> Certificate)(Rogowski, Patricia) (Entered: 07/07/2010)
REDACTED VERSION of <u>190</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0484 - MA0489, # <u>2</u> Appendix MA0490 - MA0515, # <u>3</u> Appendix MA0516 - MA0534, # <u>4</u> Appendix MA0535 - MA0541, # <u>5</u> Appendix MA0542 - MA0550, # <u>6</u> Appendix MA0551 - MA0561, # <u>7</u> Appendix MA0562 - MA0564, # <u>8</u> Appendix MA0565 - MA0569, # <u>9</u> Appendix MA0570 - MA0574, # <u>10</u> Appendix MA0575 - MA0576, # <u>11</u> Appendix MA0577 - MA0601, # <u>12</u> Appendix MA0602 - MA0603, # <u>13</u> Appendix MA0604 - MA0605, # <u>14</u> Appendix MA0606 - MA0609, # <u>15</u> Appendix MA0610 - MA0612, # <u>16</u> Appendix MA0613 - MA0625, # <u>17</u> Appendix MA0626 - MA0628, # <u>18</u> Appendix MA0629 - MA0630, # <u>19</u> Appendix MA0631 - MA0653, # <u>20</u> Appendix MA0654 - MA0685, # <u>21</u> Appendix MA0686 - MA0701, # <u>22</u> Appendix MA0702 - MA0732, # <u>23</u> Appendix MA0733 - MA0742, # <u>24</u> Appendix MA0743 - MA0750, # <u>25</u> Appendix MA0751 - MA0766, # <u>26</u> Appendix MA0767 - MA0772, # <u>27</u> Appendix MA0773 - MA0780, # <u>28</u> Appendix MA0781 - MA0807, # <u>29</u> Appendix MA0808 - MA0824, # <u>30</u> Appendix MA0825 - MA0831.1, # <u>31</u> Appendix MA0832 - MA0838, # <u>32</u> Appendix MA0839 - MA0844, # <u>33</u> Appendix MA0845 - MA0858, # <u>34</u> Appendix MA0859 - MA0868, # <u>35</u> Appendix MA0869 - MA0877, # <u>36</u> Appendix MA0878 - MA0884, # <u>37</u> Appendix MA0885 - MA0887, # <u>38</u> Appendix MA0888 - MA0891, # <u>39</u> Appendix MA0892 - MA0909, # <u>40</u> Appendix MA0910 - MA0931, # <u>41</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)
REDACTED VERSION of <u>198</u> Opening Brief in Support,, SOITEC/CEA Parties' Opening Brief In Support Of Motion For Summary Judgment: Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)
REDACTED VERSION of <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)

REDACTED VERSION of <u>192</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VI of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>193</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VIII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>194</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume X of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>195</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XVII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>196</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XIX of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
APPENDIX re <u>228</u> Claim Construction Answering Brief by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0782 - DA0783, # <u>2</u> Appendix DA0784 - DA0785, # <u>3</u> Appendix DA0786, # <u>4</u> Appendix DA0787 - DA0810, # <u>5</u> Appendix DA0811 - DA0834, # <u>6</u> Appendix DA0835 - DA0845, # <u>7</u> Appendix DA0846 - DA0855, # <u>8</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, <u>228</u> Claim Construction Answering Brief Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
APPENDIX re <u>230</u> Claim Construction Answering Brief, Appendix to Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix PA-0001 - PA-0050, # <u>2</u> Appendix PA-0051 - PA-0083, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>183</u> Appendix, Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>170</u> Exhibit to a Document, Exhibit A to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>171</u> Exhibit to a Document, Exhibit B to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)

REDACTED VERSION of <u>172</u> Exhibit to a Document, Exhibit C to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
ANSWERING BRIEF in Opposition re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
APPENDIX re <u>247</u> Answering Brief in Opposition,, Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1156) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1103 - PA-1109 - FILED UNDER SEAL, # <u>2</u> Exhibit PA-1110 - PA-1118 - FILED UNDER SEAL, # <u>3</u> Exhibit PA-1119 - PA-1130 - FILED UNDER SEAL, # <u>4</u> Exhibit PA-1131 - PA-1143 - FILED UNDER SEAL, # <u>5</u> Exhibit PA-1144 - PA-1156, # <u>6</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
APPENDIX re <u>250</u> Answering Brief in Opposition, Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1190 - PA-1191, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
REDACTED VERSION of <u>241</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>249</u> Answering Brief in Opposition, to Plaintiffs' Motion for Summary Judgment on the Infringement of U.S. Patent No. 5,834,812 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>253</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Aspar Patents Are Not Invalid for Inequitable Conduct by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)

<p>REDACTED VERSION of <u>240</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0932 - MA0985, # <u>2</u> Appendix MA0986 - MA1039.22, # <u>3</u> Appendix MA1040 - MA1144, # <u>4</u> Appendix MA1145 - MA1200, # <u>5</u> Appendix MA1201 - MA1265, # <u>6</u> Appendix MA1265.1 - MA1338, # <u>7</u> Appendix MA1339 - MA1547, # <u>8</u> Appendix MA1548 - MA1627, # <u>9</u> Appendix MA1628 - MA1693, # <u>10</u> Appendix MA1694 - MA1953, # <u>11</u> Appendix MA1954 - MA2127, # <u>12</u> Appendix MA2128 - MA2206, # <u>13</u> Appendix MA2207 - MA2253, # <u>14</u> Appendix MA2254 - MA2273, # <u>15</u> Appendix MA2274 - MA2333, # <u>16</u> Appendix MA2334 - MA2337, # <u>17</u> Appendix MA2338 - MA2342, # <u>18</u> Appendix MA2343 - MA2346, # <u>19</u> Appendix MA2347 - MA2351, # <u>20</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/26/2010) (2 parts).</p>
<p>REDACTED VERSION of <u>261</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (CORRECTED VERSION OF D.I. 241) by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>250</u> Answering Brief in Opposition, to Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>247</u> Answering Brief in Opposition,, to Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of In validity Of The Asserted Aspar Claims by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>254</u> Appendix,, to Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1143 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>251</u> Appendix,, to Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REPLY BRIEF re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)</p>
<p>DECLARATION re <u>268</u> Reply Brief, Declaration of Marcus T. Hall in Support of Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)</p>
<p>APPENDIX re <u>268</u> Reply Brief, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1261) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1199 - PA-1204, # <u>2</u> Exhibit PA-1205 - PA-1206, # <u>3</u> Exhibit PA-1206.1, # <u>4</u> Exhibit PA-1231 - PA-1237, # <u>5</u> Exhibit PA-1238 - PA-1245, # <u>6</u> Exhibit PA-1246 - PA-1257, # <u>7</u> Exhibit PA-1258 - PA-1261, # <u>8</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)</p>
<p>REPLY BRIEF re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)</p>

REPLY BRIEF re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REPLY BRIEF re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REDACTED VERSION of <u>269</u> Appendix, TO REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2453_MA2479, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>273</u> Appendix REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2352 - MA2361, # <u>3</u> Appendix MA2362 - MA2371, # <u>4</u> Appendix MA2372 - MA2381, # <u>5</u> Appendix MA2382 - MA2391, # <u>6</u> Appendix MA2392 - MA2399, # <u>7</u> Appendix MA2400 - MA2404, # <u>8</u> Appendix MA2405 - MA2422, # <u>9</u> Appendix MA2423 - MA2425, # <u>10</u> Appendix MA2426 - MA2427, # <u>11</u> Appendix MA2428 - MA2430, # <u>12</u> Appendix MA2431 - MA2440, # <u>13</u> Appendix MA2441 - MA2448, # <u>14</u> Appendix MA2449 - MA2452, # <u>15</u> Appendix MA2452.1 - MA2452.9, # <u>16</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>267</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>271</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>274</u> Appendix,, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1198 and PA-1207 - PA-1230 Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>277</u> Reply Brief, in Support of SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>278</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>279</u> Reply Brief,, in Support of Plaintiffs' Motion for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>281</u> Reply Brief, in Support of Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)



REDACTED VERSION of <u>282</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
NOTICE OF SERVICE of CD of documents MEMC0782194-MEMC0782500 and FH-1 0001 - FH-8 0067 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/16/2010)
REDACTED VERSION of <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>302</u> Declaration, of Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>303</u> Exhibit to a Document Exhibit A to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>304</u> Exhibit to a Document Exhibit B to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>305</u> Exhibit to a Document Exhibit C to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>306</u> Exhibit to a Document Exhibit D to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
Proposed Pretrial Order [Proposed] Joint Pretrial Order (FILED UNDER SEAL) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1 (Sealed), # <u>2</u> Exhibit 2A (Sealed), # <u>3</u> Exhibit 2B (Sealed), # <u>4</u> Exhibit 3A (Sealed), # <u>5</u> Exhibit 3B (Sealed), # <u>6</u> Exhibit 4A (Sealed), # <u>7</u> Exhibit 4B (Sealed), # <u>8</u> Exhibit 4C (Sealed), # <u>9</u> Exhibit 5A (Sealed), # <u>10</u> Exhibit 5B (Sealed), # <u>11</u> Exhibit 6A (Sealed), # <u>12</u> Exhibit 6B (Sealed), # <u>13</u> Exhibit 7A (Sealed), # <u>14</u> Exhibit 7B (Sealed), # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/07/2010)
Proposed Voir Dire by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
VERDICT SHEET by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
Proposed Voir Dire by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)
VERDICT SHEET by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)
Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)
Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)

<p>REDACTED VERSION of <u>315</u> Proposed Pretrial Order,, Redacted Version of [Proposed] Joint Pretrial Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2A, # <u>3</u> Exhibit 2B, # <u>4</u> Exhibit 3A, # <u>5</u> Exhibit 3B, # <u>6</u> Exhibit 4A, # <u>7</u> Exhibit 4B, # <u>8</u> Exhibit 4C, # <u>9</u> Exhibit 5A, # <u>10</u> Exhibit 5B, # <u>11</u> Exhibit 6A, # <u>12</u> Exhibit 6B, # <u>13</u> Exhibit 7A, # <u>14</u> Exhibit 7B, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/13/2010)</p>
<p>MEMORANDUM OPINION. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)</p>
<p>ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)</p>
<p>MEMORANDUM ORDER re: claim construction. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010) ORAL ORDER by Judge Sue L. Robinson on 10/14/2010 that the responses to the issues raised in the exhibits to the joint pre-trial order are to be stricken from the record. (These filings, formerly D.I. Nos. 318 and 323 have been deleted from the docket.) (nmf) (Entered: 10/14/2010)</p>
<p>AMENDED ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; *granting* <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/14/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Final Pretrial Conference held on 10/14/2010. (Court Reporter V. Gunning.) (nmf) (Entered: 10/15/2010) SO ORDERED, re <u>315</u> Proposed Pretrial Order. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/15/2010)</p>
<p>MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/18/2010)</p>
<p>SECOND AMENDED ORDER re: <u>325</u> denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment **with respect to the '484 patent and with respect to its current process, and denied in other respects; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)</p>
<p>MEMORANDUM ORDER granting <u>329</u> MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)</p>
<p>STIPULATION MEMC's Declaratory Judgment counterclaim asserting invalidity of United States Reissued Patent No. 39,484 in Civil Action No. 1:08-292-SLR is dismissed without prejudice by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (nmf, ). (Entered: 10/21/2010)</p>

STIPULATION of Fact re <u>331</u> Memorandum and Order, <u>327</u> Memorandum and Order, <u>325</u> Memorandum Opinion by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/21/2010)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Mutually agreed upon narrowing of the issues for trial - re <u>333</u> Stipulation, <u>332</u> Stipulation,. (Kraft, Denise) (Entered: 10/21/2010) CORRECTING ENTRY: The pdf of D.I. <u>332</u> has been replaced with the correct pdf of the stipulation per request of filer. (nmf) (Entered: 10/22/2010) SO ORDERED, re <u>333</u> Stipulation filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique, <u>332</u> Stipulation, filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. Signed by Judge Sue L. Robinson on 10/22/2010. (nmf) (Entered: 10/22/2010)
Voir Dire Questions. Read in Open Court 10/25/2010.(nmf) (Entered: 10/25/2010)
Preliminary Jury Instructions. Read in Open Court 10/25/2010. (nmf) (Entered: 10/25/2010) Minute Entry for proceedings held before Judge Sue L. Robinson: Jury Trial Day 1 held on 10/25/2010. (Court Reporter Valerie Gunning, Brian Gaffigan.) (dlk) (Entered: 10/26/2010)
PLAINTIFF'S BENCH MEMORANDUM. Filed in Court 10/26/2010. (nmf) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial (Day 2) held on 10/26/2010. (Court Reporter Valerie Gunning, Kevin Maurer.) (dlk) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 3, held on 10/27/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 10/27/2010)
STATEMENT -- BENCH MEMORANDUM SUPPORTING MEMC'S PROFFER OF ADMISSIONS BY SOITEC IN PRIOR LAWSUIT INVOLVING THE '564 PATENT submitted at trial by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A)(Rogowski, Patricia) (Entered: 10/28/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 4 held on 10/28/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 11/01/2010)
Final Jury Instructions read in open Court by Judge Robinson. (lid) (Entered: 11/01/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial held on 11/1/2010. (DAY 5) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial completed on 11/2/2010. (DAY 6) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010)
REDACTED VERSION of <u>342</u> Jury Verdict. (lid) (Entered: 11/02/2010)
STATEMENT Bench Memorandum in Support of Plaintiffs' Motion For Judgment as a Matter of Law of No Unenforceability of the '009 Patent Due To Inequitable Conduct submitted at trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/02/2010)
ANSWERING BRIEF in Opposition re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order (MEMC'S OPPOSITION TO PLAINTIFFS' MOTION FOR REARGUMENT RE: MODIFICATION OF THE PROTECTIVE ORDER) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 11/22/2010. (Attachments: # <u>1</u> Exhibit 1 through 5, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 11/12/2010)
JUDGMENT in favor of defendant MEMC Electronic Materials, Inc. and against plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives as to the 812 patent. IT IS FURTHER ORDERED that judgment be and is hereby entered in favor of plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives and against defendant MEMC Electronic Materials, Inc. as to the 009 patent. Signed by Judge Sue L. Robinson on 11/15/2010. (nmf) (Entered: 11/15/2010)
STIPULATION Setting Post-Trial Briefing Schedule re <u>348</u> Judgment,, by Commissariat a LEnergie Atomique, MEMC Electronic Materials Inc., SOITEC Silicon On Insulator Technologies SA. (Rogowski, Patricia) (Entered: 11/15/2010)

MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 11/16/2010) SO ORDERED- re <u>349</u> Stipulation. Set POST TRIAL Briefing Schedule: (Opening Brief due 12/8/2010., Answering Brief due 12/29/2010., Reply Brief due 1/12/2010.). Signed by Judge Sue L. Robinson on 11/17/2010. (lid) (Entered: 11/17/2010)
MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
OPENING BRIEF in Support re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order, <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 12/10/2010. (Attachments: # <u>1</u> Appendix A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
STIPULATION TO EXTEND TIME Respond to MEMC's Motion for Reargument of the Court's Order Re: Unenforceability of the '009 Patent to December 3, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/24/2010) SO ORDERED- re <u>353</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,. (Answering Brief due 12/3/2010.). Signed by Judge Sue L. Robinson on 11/30/2010. (lid) (Entered: 11/30/2010)
STIPULATION TO EXTEND TIME to file Motions and Opening Post-Trial Briefs to December 13, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/03/2010)
REPLY BRIEF re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/03/2010) SO ORDERED- re <u>354</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (POST TRIAL Opening Brief due 12/13/2010.). Signed by Judge Sue L. Robinson on 12/6/2010. (lid) (Entered: 12/06/2010)
EXHIBIT re <u>355</u> Reply Brief, Exhibit B to Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/06/2010)
ANSWERING BRIEF in Opposition re <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 12/20/2010. (Rogowski, Patricia) (Entered: 12/10/2010)
STIPULATION TO EXTEND TIME Stipulation and Order for Plaintiffs to file Motions and Opening Post-Trial Briefs to December 14, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/13/2010)
MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/13/2010)
OPENING BRIEF in Support re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 12/30/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 12/13/2010)

MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
OPENING BRIEF in Support re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 1/3/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
MOTION For Injunctive Relief Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
STIPULATION TO EXTEND TIME due date for Answering and Reply Post-Trial Briefs to January 7, 2011 for Answering Brief and January 21, 2011 for Reply Brief - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/15/2010) SO ORDERED- re <u>365</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (Answering Post trial Brief due 1/7/2011., Reply post trial Brief due 1/21/2011.). Signed by Judge Sue L. Robinson on 12/16/2010. (lid) (Entered: 12/17/2010)
STIPULATION TO EXTEND TIME Post-Trial Answering Briefs to January 12, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/06/2011)
NOTICE of Appearance by Aleine Michelle Porterfield on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc. (Attachments: # <u>1</u> Certificate of Service)(Porterfield, Aleine) (Entered: 01/07/2011)
Joint STIPULATION TO EXTEND TIME Post-trial Answering Briefs and Post-trial Reply Briefs to January 14, 2011 and January 28, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/12/2011)
ANSWERING BRIEF in Opposition re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/14/2011)
ANSWERING BRIEF in Opposition re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial (MEMCS ANSWERING BRIEF IN OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011)
DECLARATION re <u>378</u> Answering Brief in Opposition, (DECLARATION OF ROBERT M. EVANS, JR. IN SUPPORT OF MEMCS OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011)
REDACTED VERSION of <u>376</u> Answering Brief in Opposition, to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)
REDACTED VERSION of <u>377</u> Appendix to MEMC's Answering Brief in Opposition to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1-7, # <u>2</u> Exhibit 8, # <u>3</u> Exhibit 9, # <u>4</u> Exhibit 10, # <u>5</u> Exhibit 11, # <u>6</u> Exhibit 12-13, # <u>7</u> Exhibit 14, # <u>8</u> Exhibit 15, # <u>9</u> Exhibit 16, # <u>10</u> Exhibit 17, # <u>11</u> Exhibit 18, # <u>12</u> Exhibit 19, # <u>13</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)

Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Tuesday, February 1, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/28/2011)
Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Friday, February 4, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/31/2011)
REDACTED VERSION of <u>364</u> Opening Brief in Support,,,. Redacted Version of Opening Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Exhibit O, # <u>16</u> Exhibit P, # <u>17</u> Exhibit Q, # <u>18</u> Exhibit R, # <u>19</u> Exhibit S)(Kraft, Denise) (Entered: 02/02/2011)
REPLY BRIEF re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 02/04/2011)
REPLY BRIEF re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
DECLARATION re <u>387</u> Reply Brief, Declaration of Michael L. Brody in Support of Reply Brief In Support of Plaintiffs' Renewed Motion For Judgment as a Matter of Law or In The Alternative For a New Trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
OPENING BRIEF in Support re <u>390</u> MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 2/25/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
DECLARATION re <u>391</u> Opening Brief in Support,, Declaration of Marcus T. Hall in Support of Plaintiffs' Opening Brief in Support of Motion to Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
REDACTED VERSION of <u>389</u> Reply Brief, Redacted Version of Reply Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 02/09/2011)

ANSWERING BRIEF in Opposition re 390 MOTION to Strike 386 Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike 386 Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 2/28/2011. (Attachments: # 1 Exhibit 1-3, # 2 Certificate of Service)(Rogowski, Patricia) (Entered: 02/18/2011)

REPLY BRIEF re 390 MOTION to Strike 386 Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike 386 Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 02/28/2011)

Applicants are enclosing Form PTO-1449(forty-five), along with a copy of each listed reference for which a copy is required under 37 CFR §1.98(a)(2). Pursuant to the undersigned attorney's obligation and duties under 37 CFR §§ 1.56 and 1.98(a)(3) and (c), either English language abstracts, partial translations, or full translations are included for patent documents which are not in English for the express purpose of providing a concise explanation of the references to the Patent and Trademark Office with the opportunity to evaluate the same.

References D407 – D436 are cited in accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and, more particularly, in accordance with 37 C.F.R. §1.97(b). These documents are litigation documents filed by the parties in *SOITEC SA v. SILICON GENESIS* (2003-1080) in the U.S. Court of Appeal for the Federal Circuit. This litigation involved U.S. Pat. No. 5,374,564, owned by the assignee of record herein.

References D437 – D607 are cited in accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and, more particularly, in accordance with 37 C.F.R. §1.97(b). These documents are litigation documents filed by the parties in *SOITEC SA v. MEMC* (1:08-cv-00292-SLR) in the U.S. District Court, District of Delaware. This lawsuit involves patents owned by the assignee of record, including Re39,484, which is a reissue patent of U.S. Pat. No. 5,374,564, and including other patents that disclose subject matter that may be related to that claimed in the above-

referenced patent application. Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 CFR §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 CFR §1.56(a).

The Applicant or Applicants have calculated no fee to be due in connection with the filing of this Information Disclosure Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Information Disclosure Statement to a deposit account, as authorized in the Transmittal accompanying this Information Disclosure Statement.

Respectfully submitted,

April 26, 2011

Date

/Jasper W. Dockrey/

Jasper W. Dockrey  
(Reg. No. 33,868)